

走査透過電子顕微鏡

HD-2700

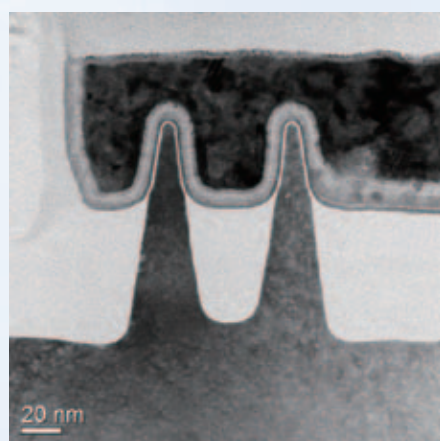
200 kV Scanning Transmission Electron Microscope

デュアルEDXによる超高感度EDX分析と 高分解能STEM観察によるデバイス解析

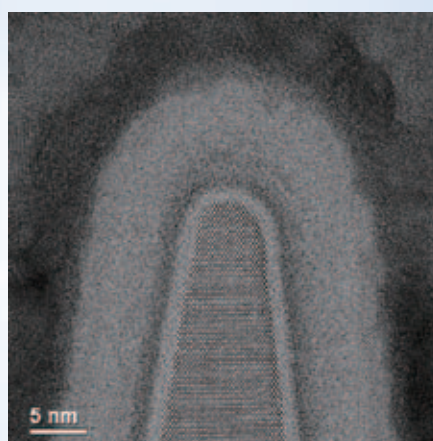


Elemental analysis and STEM imaging of Device using STEM with Dual SDD

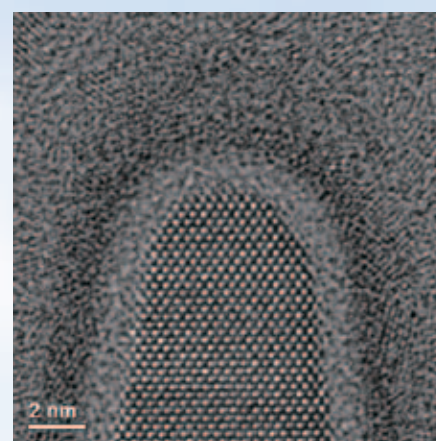
◎ Fin-FET Deviceの高分解能STEM明視野像 STEM Bright Field images of Fin-FET Device



(a) BF-STEM : $\times 400,000$



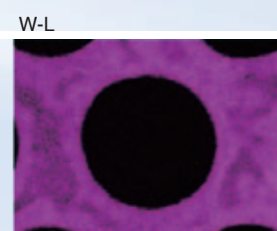
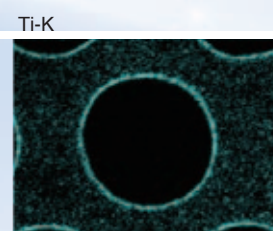
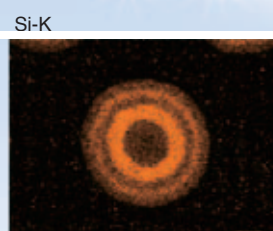
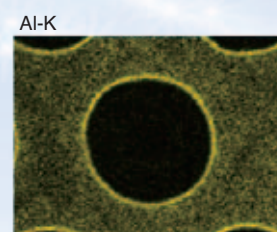
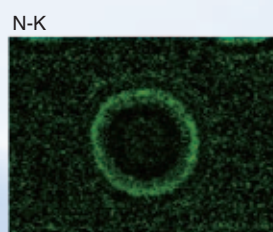
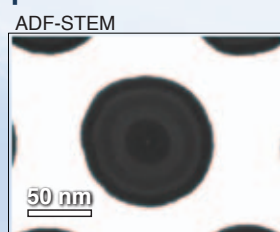
(b) BF-STEM : $\times 2,000,000$



(c) BF-STEM : $\times 5,000,000$

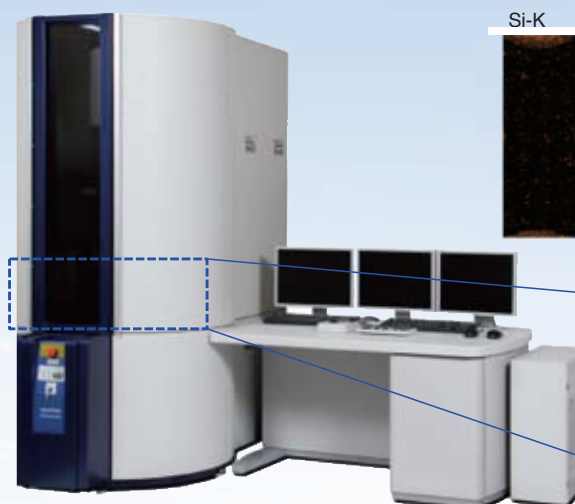
Specimen : Fin-FET device
Vacc : 200 kV

◎ 3D-NAND Deviceの元素分析マップ Elemental maps of 3D-NAND device



Elemental maps using HD-2700 with dual Silicon Drift Detector

Specimen : 3D-NAND Device
Vacc : 200 kV
Magnification : 3,000,000
Acquisition time : 10 min



HD-2700 with Dual Solid Drift Detector

